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L Number	Hits	Search Text	DB	Time stamp
1	1672	118/719.ccls.	USPAT;	2004/01/09 20:14
			US-PGPUB;	
			ЕРО; ЛРО;	
ļ			DERWENT;	
			IBM_TDB	
2	2090	29/25.01.ccls.	USPAT;	2004/01/09 20:07
		,	US-PGPUB;	
			ЕРО; ЛРО;	
			DERWENT;	
,	333	427/9.ccls.	IBM_TDB USPAT;	2004/01/09 20:07
3	333	42779.0015.	US-PGPUB;	2004/01/07 20:07
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
4	6936	438/5-18.ccls.	USPAT;	2004/01/09 20:07
			US-PGPUB;	
		ŕ	ЕРО; ЛРО;	
			DERWENT;	
			IBM_TDB	
5	2423	700/19,49,52,99-104,108-111,119-121,123.ccls.	USPAT;	2004/01/09 20:08
			US-PGPUB;	
			ЕРО; ЛРО;	
			DERWENT;	
	004	1115	IBM_TDB USPAT;	2004/01/09 20:08
6	894	L1-L5	US-PGPUB;	2004/01/09 20.08
			EPO; JPO;	
1		·	DERWENT;	
			IBM TDB	
7	13149	118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or	USPAT;	2004/01/09 20:08
'	13117	700/19,49,52,99-104,108-111,119-121,123.ccls.	US-PGPUB;	
		, , , , , , , , , , , , , , , , , , , ,	ЕРО, ЛРО,	
		•	DERWENT;	
			IBM_TDB	
8	1237213	((semiconductor or (semi adj conductor) or semi-conductor or wafer or	USPAT;	2004/01/09 20:39
		IC or (integrated adj circuit) or lot or (micro adj electronic) or	US-PGPUB;	
		microelectronic or memory or (logic adj unit) or microprocessor) with	ЕРО; ЈРО;	
		(process\$3 or fabricat\$3 or produc\$4 or manufactur\$3 or making))	DERWENT;	
	7/02	(110/710 calc. or 20/25 01 calc. or 427/0 calc. or 429/5 19 calc. or	IBM_TDB USPAT;	2004/01/09 20:40
9	7683	(118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor	US-PGPUB;	2004/01/07 20.40
		or (semi adj conductor) or semi-conductor or wafer or IC or (integrated	EPO; JPO;	
		adj circuit) or lot or (micro adj electronic) or microelectronic or memory	DERWENT;	
	_	or (logic adj unit) or microprocessor) with (process\$3 or fabricat\$3 or	IBM_TDB	
		produc\$4 or manufactur\$3 or making)))	_	
10	1146265	((semiconductor or (semi adj conductor) or semi-conductor or wafer or	USPAT;	2004/01/09 20:41
		IC or (integrated adj circuit) or lot or (micro adj electronic) or	US-PGPUB;	
		microelectronic or memory or (logic adj unit) or microprocessor or	ЕРО; ЈРО;	
		process\$3 or fabricat\$3 or produc\$4 or manufactur\$3) with (deposit\$3	DERWENT;	
l		or etch\$3 or metrology or measur\$3 or tool\$3))	IBM_TDB	2004/01/00 20:16
11	5313	((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or	USPAT; US-PGPUB;	2004/01/09 20:16
1		700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor	EPO; JPO;	
		or (semi adj conductor) or semi-conductor or wafer or IC or (integrated adj circuit) or lot or (micro adj electronic) or microelectronic or memory	DERWENT;	
		or (logic adj unit) or microprocessor) with (process\$3 or fabricat\$3 or	IBM_TDB	
		produc\$4 or manufactur\$3 or making)))) and (((semiconductor or (semi		
		adj conductor) or semi-conductor or wafer or IC or (integrated adj		
		circuit) or lot or (micro adj electronic) or microelectronic or memory or		
		(logic adj unit) or microprocessor or process\$3 or fabricat\$3 or produc\$4		
-		or manufactur\$3) with (deposit\$3 or etch\$3 or metrology or measur\$3 or		
		tool\$3)))	1	

12	1860420	((semiconductor or (semi adj conductor) or semi-conductor or wafer or	USPAT;	2004/01/09 20:44
12	1000.20	IC or (integrated adj circuit) or lot or (micro adj electronic) or microelectronic or memory or (logic adj unit) or microprocessor or	US-PGPUB; EPO; JPO;	200 1101107 20.17
		process\$3 or fabricat\$3 or produc\$4 or manufactur\$3 or deposit\$3 or	DERWENT;	
		etch\$3 or metrology or measur\$3 or tool\$3) with (((process\$3 or cycle or	IBM_TDB	
		average or mean) near3 (time or rate)) or uniform\$3 or thickness or		
		(critical adj dimension\$3) or CD or variability or target or accura\$4 or		
12	4526	defect\$5)) (((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or	USPAT;	2004/01/09 20:23
13	4320	700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor	US-PGPUB;	2004/01/09 20.23
		or (semi adj conductor) or semi-conductor or wafer or IC or (integrated	EPO; JPO;	
		adj circuit) or lot or (micro adj electronic) or microelectronic or memory	DERWENT;	
	- }	or (logic adj unit) or microprocessor) with (process\$3 or fabricat\$3 or	IBM_TDB	
	1	produc\$4 or manufactur\$3 or making)))) and (((semiconductor or (semi		
		adj conductor) or semi-conductor or wafer or IC or (integrated adj circuit) or lot or (micro adj electronic) or microelectronic or memory or		
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		or manufactur\$3) with (deposit\$3 or etch\$3 or metrology or measur\$3 or		
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		(((process\$3 or cycle or average or mean) near3 (time or rate)) or		
		uniform\$3 or thickness or (critical adj dimension\$3) or CD or variability		
		or target or accura\$4 or defect\$5)))		
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		29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor	US-PGPUB; EPO; JPO;	
		or (semi adj conductor) or semi-conductor or wafer or IC or (integrated	DERWENT;	
		adj circuit) or lot or (micro adj electronic) or microelectronic or memory	IBM_TDB	
1		or (logic adj unit) or microprocessor) with (process\$3 or fabricat\$3 or	_	
		produc\$4 or manufactur\$3 or making)))) and (((semiconductor or (semi		
		adj conductor) or semi-conductor or wafer or IC or (integrated adj circuit) or lot or (micro adj electronic) or microelectronic or memory or		
		(logic adj unit) or microprocessor or process\$3 or fabricat\$3 or produc\$4		
		or manufactur\$3) with (deposit\$3 or etch\$3 or metrology or measur\$3 or		
		tool\$3)))) and (((semiconductor or (semi adj conductor) or		
		semi-conductor or wafer or IC or (integrated adj circuit) or lot or (micro		
		adj electronic) or microelectronic or memory or (logic adj unit) or microprocessor or process\$3 or fabricat\$3 or produc\$4 or manufactur\$3		
		or deposit\$3 or etch\$3 or metrology or measur\$3 or tool\$3) with		
		(((process\$3 or cycle or average or mean) near3 (time or rate)) or		<i>.</i>
		uniform\$3 or thickness or (critical adj dimension\$3) or CD or variability		
		or target or accura\$4 or defect\$5))))		
15	560847	((semiconductor or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or fabricat\$3 or production or manufactur\$3))	USPAT; US-PGPUB;	2004/01/09 20:40
		with (process\$3 or faoricat\$3 or production of manufactur\$3))	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
16	6256	(118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or	USPAT;	2004/01/09 20:40
		700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or	US-PGPUB;	
		fabricat\$3 or production or manufactur\$3)))	EPO; JPO; DERWENT;	
		Additional of production of intentational party	IBM_TDB	
17	2140	((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or	USPAT;	2004/01/09 20:50
		700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor	US-PGPUB;	
		or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or	EPO; JPO;	
		fabricat\$3 or production or manufactur\$3)))) and ((tool\$3 or chamber or processor) with (deposit\$3 or etch\$3 or metrology or measur\$3 or	DERWENT; IBM_TDB	
		polish\$3 or lithography or exposure or oxidation or oxidizing or	12.11_122	
		implant\$5 or planariz\$5 or CVD or vapor-deposit\$3 or chemical-vapor		
		or clean\$3))		

18	873	(((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or	USPAT;	2004/01/09 21:03
		700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor	US-PGPUB;	
		or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or	ЕРО; ЈРО;	
	1	fabricat\$3 or production or manufactur\$3)))) and ((tool\$3 or chamber or	DERWENT;	
		processor) with (deposit\$3 or etch\$3 or metrology or measur\$3 or	IBM_TDB	
•		polish\$3 or lithography or exposure or oxidation or oxidizing or		
		implant\$5 or planariz\$5 or CVD or vapor-deposit\$3 or chemical-vapor		
		or clean\$3))) and (chamber with (((process\$3 or cycle or average or		
		mean) near3 (time or rate)) or uniform\$3 or thickness or (critical adj		
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19	113	700/19,49,52,99-104,108-111,119-121,123.ccls. and ((((118/719.ccls. or	USPAT;	2004/01/09 20:45
		29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or	US-PGPUB;	
		700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor	ЕРО; ЈРО;	
		or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or	DERWENT;	
		fabricat\$3 or production or manufactur\$3)))) and ((tool\$3 or chamber or	IBM_TDB	
	•	processor) with (deposit\$3 or etch\$3 or metrology or measur\$3 or	12111_122	
		polish\$3 or lithography or exposure or oxidation or oxidizing or		
		implant\$5 or planariz\$5 or CVD or vapor-deposit\$3 or chemical-vapor		
		or clean\$3))) and (chamber with (((process\$3 or cycle or average or		
		mean) near3 (time or rate)) or uniform\$3 or thickness or (critical adj		
		dimension\$3) or CD or variability or target or accura\$4 or defect\$5)))		
20	1804	((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or	USPAT;	2004/01/09 20:50
20	1004	700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor		2004/01/09 20.30
			US-PGPUB;	
		or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or	ЕРО; ЛРО;	
		fabricat\$3 or production or manufactur\$3)))) and ((tool\$3 or chamber or	DERWENT;	
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21	581	(((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or	USPAT;	2004/01/09 20:51
		700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor	US-PGPUB;	
		or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or	EPO; JPO;	
		fabricat\$3 or production or manufactur\$3)))) and ((tool\$3 or chamber or	DERWENT;	
	.	processor) with (deposit\$3 or etch\$3 or metrology or measur\$3))) and	IBM_TDB	
		(chamber near5 (((process\$3 or cycle or average or mean) near3 (time or		
		rate)) or uniform\$3 or thickness or (critical adj dimension\$3) or CD or		
		variability or target or accura\$4 or defect\$5))		•
22	263	((((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or	USPAT;	2004/01/09 21:10
į		700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor	US-PGPUB;	
i		or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or	ЕРО; ЛРО;	
,		fabricat\$3 or production or manufactur\$3)))) and ((tool\$3 or chamber or	DERWENT;	
		processor) with (deposit\$3 or etch\$3 or metrology or measur\$3))) and	IBM_TDB	
		(chamber near5 (((process\$3 or cycle or average or mean) near3 (time or		
		rate)) or uniform\$3 or thickness or (critical adj dimension\$3) or CD or		
		variability or target or accura\$4 or defect\$5))) and (@pd<=20000813)		
23	439	((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or	USPAT;	2004/01/09 21:37
		700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor	US-PGPUB;	
	j j	or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or	ЕРО; ЛРО;	
		fabricat\$3 or production or manufactur\$3)))) and (chamber with	DERWENT;	
		(((process\$3 or cycle or average or mean) near3 (time or rate)) or	IBM_TDB	
		(defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or		
		(critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or		
·		precision) near3 process\$3)))		
24	167	((((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or	USPAT;	2004/01/09 21:37
		700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor	US-PGPUB;	
		or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or	ЕРО; ЛРО;	
		fabricat\$3 or production or manufactur\$3)))) and (chamber with	DERWENT;	
		((((process\$3 or cycle or average or mean) near3 (time or rate)) or	IBM_TDB	•
		(defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or		
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		precision) near3 process\$3)))) and (@pd<=20000813)		
		,		'

25	23	((((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or	USPAT;	2004/01/09 21:34
		700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or fabricat\$3 or production or manufactur\$3)))) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
26	272	precision) near3 process\$3)))) and (@pd<=20000813)) and (software) ((((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or fabricat\$3 or production or manufactur\$3)))) and (chamber with	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/01/09 21:34
27	55	((((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or precision) near3 process\$3)))) not ((((118/719.ccls. or 29/25.01.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or fabricat\$3 or production or manufactur\$3)))) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or precision) near3 process\$3)))) and (@pd<=20000813)) ((((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or fabricat\$3 or production or manufactur\$3)))) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or precision) near3 process\$3)))) not ((((118/719.ccls. or 29/25.01.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or fabricat\$3 or production or manufactur\$3)))) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or precision) near3 process\$3)))) and (@pd<=20000813))) and (applied adj or	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 21:37
28	513	materials) as. (118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 21:51
29	78	precision) near3 process\$3))) ((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or precision) near3 process\$3)))) and (applied adj materials).as.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/01/09 21:37
30	23	((((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/01/09 21:37
		(critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or precision) near3 process\$3)))) and (applied adj materials).as.) and (@pd<=20000813)	IBM_TDB	•

31	55	(((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or	USPAT;	2004/01/09 21:38
31	"	700/19,49,52,99-104,108-111,119-121,123.ccls.) and (chamber with	US-PGPUB;	2004/01/09 21.38
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-		(defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or	DERWENT;	
		(critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or	IBM TDB	•
		precision) near3 process\$3)))) and (applied adj materials).as.) not	- ,	
		(((((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or		
		700/19,49,52,99-104,108-111,119-121,123.ccls.) and (chamber with		
		(((process\$3 or cycle or average or mean) near3 (time or rate)) or		
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32	55	((((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or	USPAT;	2004/01/09 22:23
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	1	(defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or	DERWENT;	
		(critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or	IBM_TDB	
		precision) near3 process\$3)))) and (applied adj materials).as.) not		
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	1			
		(@pd<=20000813))) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or		
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		or value)) or ((accura\$4 or precision) near3 process\$3))).clm		
33	12	(((((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or	USPAT;	2004/01/09 21:52
33	"2	700/19,49,52,99-104,108-111,119-121,123.ccls.) and (chamber with	US-PGPUB;	200 11 01 10 21 10 2
		(((process\$3 or cycle or average or mean) near3 (time or rate)) or	EPO; JPO;	
		(defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or	DERWENT;	
		(critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or	IBM TDB	
		precision) near3 process\$3)))) and (applied adj materials).as.) not	_	
		(((((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or		
		700/19,49,52,99-104,108-111,119-121,123.ccls.) and (chamber with		
		(((process\$3 or cycle or average or mean) near3 (time or rate)) or		
		(defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or		
		(critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or		
		precision) near3 process\$3)))) and (applied adj materials).as.) and		
		(@pd<=20000813))) and (chamber with (((process\$3 or cycle or average		
		or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or		
		variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target	,	•
20		or value)) or ((accura\$4 or precision) near3 process\$3))).clm.	LIODAT:	2004/01/00 22:24
38	55	((((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or	USPAT;	2004/01/09 22:24
		700/19,49,52,99-104,108-111,119-121,123.ccls.) and (chamber with	US-PGPUB; EPO; JPO;	
		(((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or	DERWENT;	
		(critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or	IBM TDB	
		precision) near3 process\$3)))) and (applied adj materials).as.) not	IDW_TDD	
		((((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or		
	1	700/19,49,52,99-104,108-111,119-121,123.ccls.) and (chamber with		
		(((process\$3 or cycle or average or mean) near3 (time or rate)) or		
		(defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or		
		(critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or		
		precision) near3 process\$3)))) and (applied adj materials).as.) and		
		(@pd<=20000813))) and (chamber with (((process\$3 or cycle or average		
		or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or		
		variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target		
		or value or parameter)) or ((accura\$4) near3 (process\$3 or tool or		
]	chamber)))).clm		

39	1582	(chamber with (((process\$3 or cycle or average or mean) near3 (time or	USPAT;	2004/01/09 22:28
		rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3	US-PGPUB;	
		(thickness or (critical adj dimension\$3) or CD or target or value or	ЕРО; ЈРО;	
		parameter)) or ((accura\$4) near3 (process\$3 or tool or chamber)))).clm.	DERWENT;	
40	-,	(/ 1 - 1	IBM_TDB	2004/01/00 22:21
40	74	((chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3	USPAT; US-PGPUB;	2004/01/09 22:31
		(thickness or (critical adj dimension\$3) or CD or target or value or	EPO; JPO;	
		parameter)) or ((accura\$4) near3 (process\$3 or tool or chamber)))).clm.)	DERWENT;	
		and (118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or	IBM_TDB	
		700/19,49,52,99-104,108-111,119-121,123.ccls.)	15111_155	
41	54	(chamber with (determin\$5 or comput\$5 or calculat\$3) with	USPAT;	2004/01/09 22:31
		(((process\$3 or cycle or average or mean) near3 (time or rate)) or	US-PGPUB;	
		(defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or	ЕРО; ЛРО;	
		(critical adj dimension\$3) or CD or target or value or parameter)) or	DERWENT,	
		((accura\$4) near3 (process\$3 or tool or chamber)))).clm. and software	IBM_TDB	
42	18	((chamber with (determin\$5 or comput\$5 or calculat\$3) with	USPAT;	2004/01/09 22:31
		(((process\$3 or cycle or average or mean) near3 (time or rate)) or	US-PGPUB;	
		(defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or	ЕРО; ЛРО;	
		(critical adj dimension\$3) or CD or target or value or parameter)) or	DERWENT;	
		((accura\$4) near3 (process\$3 or tool or chamber)))).clm. and software)	IBM_TDB	
		and (118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or		
12	152	700/19,49,52,99-104,108-111,119-121,123.ccls.)	USPAT;	2004/01/09 22:31
43	153	(chamber with (determin\$5 or comput\$5 or calculat\$3) with (((process\$3 or cycle or average or mean) near3 (time or rate)) or	US-PGPUB;	2004/01/09 22.31
		((threess of cycle of average of fical) ficals (time of rate)) of (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or	EPO; JPO;	
		(critical adj dimension\$3) or CD or target or value or parameter)) or	DERWENT;	
		((accura\$4) near3 (process\$3 or tool or chamber)))).clm.	IBM_TDB	
45	36	((chamber with (determin\$5 or comput\$5 or calculat\$3) with	USPAT;	2004/01/09 22:32
		(((process\$3 or cycle or average or mean) near3 (time or rate)) or	US-PGPUB;	
	,	(defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or	ЕРО; ЈРО;	
		(critical adj dimension\$3) or CD or target or value or parameter)) or	DERWENT;	
		((accura\$4) near3 (process\$3 or tool or chamber)))).clm. and software)	IBM_TDB	
		not (((chamber with (determin\$5 or comput\$5 or calculat\$3) with		
		(((process\$3 or cycle or average or mean) near3 (time or rate)) or		
	}	(defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or		
		(critical adj dimension\$3) or CD or target or value or parameter)) or ((accura\$4) near3 (process\$3 or tool or chamber)))).clm. and software)		
		and (118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or	•	
		700/19,49,52,99-104,108-111,119-121,123.ccls.))		
44	2.5	((chamber with (determin\$5 or comput\$5 or calculat\$3) with	USPAT;	2004/01/09 22:46
.,		(((process\$3 or cycle or average or mean) near3 (time or rate)) or	US-PGPUB;	
		(defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or	ЕРО; ЛРО;	·
		(critical adj dimension\$3) or CD or target or value or parameter)) or	DERWENT;	
		((accura\$4) near3 (process\$3 or tool or chamber)))).clm.) and	IBM_TDB	
		(118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or		
		700/19,49,52,99-104,108-111,119-121,123.ccls.)		
46]. 7	(((chamber with (determin\$5 or comput\$5 or calculat\$3) with	USPAT;	2004/01/09 22:46
		(((process\$3 or cycle or average or mean) near3 (time or rate)) or	US-PGPUB;	
		(defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value or parameter)) or	EPO; JPO; DERWENT;	
		((accura\$4) near3 (process\$3 or tool or chamber)))).clm.) and	IBM_TDB	
		(118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or	1011-100	
		700/19,49,52,99-104,108-111,119-121,123.ccls.)) not ((chamber with		
		(determin\$5 or comput\$5 or calculat\$3) with (((process\$3 or cycle or		
		average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or		
		((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3)		
		or CD or target or value or parameter)) or ((accura\$4) near3 (process\$3		
	,	or tool or chamber)))).clm. and software)		
-	2	20030029383.pn.	USPAT;	2004/01/09 20:06
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
L			IBM_TDB	<u></u>